


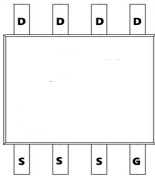
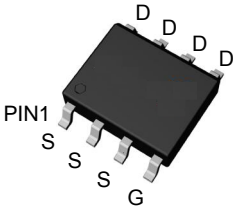
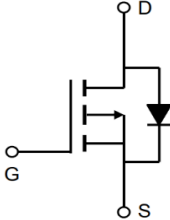


**TM20P03S**

**P-Channel Enhancement Mosfet**

<p><b>General Description</b></p> <ul style="list-style-type: none"> <li>• Low <math>R_{DS(ON)}</math></li> <li>• RoHS and Halogen-Free Compliant</li> </ul> <p><b>Applications</b></p> <ul style="list-style-type: none"> <li>• Load switch</li> <li>• PWM</li> </ul>	<p><b>General Features</b></p> <p><math>V_{DS} = -30V</math> <math>I_D = -20A</math>  <math>R_{DS(ON)} = 6.8m\Omega</math> (typ.) @ <math>V_{GS} = -10V</math></p> <p>100% UIS Tested          100% <math>R_g</math> Tested</p> 
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S:SOP-8L

Marking: 4409

**Absolute Maximum Ratings** ( $T_A = 25^\circ C$  unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source voltage	$V_{DS}$	-30	V
Gate-Source voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	$T_A = 25^\circ C$	-20
		$T_A = 100^\circ C$	-13
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	-74	A
Single Pulse Avalanche Energy <sup>2</sup>	<b>EAS</b>	80	mJ
Total Power Dissipation	$T_A = 25^\circ C$	$P_D$	3
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient <sup>3</sup>	$R_{\theta JA}$	41.6	$^\circ C/W$



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**Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise noted)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	<b>V<sub>(BR)DSS</sub></b>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30	-	-	V
Gate-body Leakage current	<b>I<sub>gss</sub></b>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T <sub>J</sub> =25°C	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V	-	-	-1	μA
	T <sub>J</sub> =100°C		-	-	-100	
Gate-Threshold Voltage	<b>V<sub>GS(th)</sub></b>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1.0	-1.8	-2.5	V
Drain-Source On-Resistance <sup>4</sup>	<b>R<sub>DS(on)</sub></b>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -12A	-	6.8	10	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A	-	11	13	
Forward Transconductance <sup>4</sup>	<b>g<sub>fs</sub></b>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -10A	-	50	-	S
<b>Dynamic Characteristics<sup>5</sup></b>						
Input Capacitance	<b>C<sub>iss</sub></b>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz	-	2200	-	pF
Output Capacitance	<b>C<sub>oss</sub></b>		-	430	-	
Reverse Transfer Capacitance	<b>C<sub>rss</sub></b>		-	358	-	
Gate Resistance	<b>R<sub>g</sub></b>	f=1MHz	-	9.5	-	Ω
<b>Switching Characteristics<sup>5</sup></b>						
Total Gate Charge	<b>Q<sub>g</sub></b>	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -15V I <sub>D</sub> = -12A	-	35	-	nC
Gate-Source Charge	<b>Q<sub>gs</sub></b>		-	9.9	-	
Gate-Drain Charge	<b>Q<sub>gd</sub></b>		-	10.5	-	
Turn-On Delay Time	<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = -10V, V <sub>DD</sub> = -15V R <sub>G</sub> = 3Ω, I <sub>D</sub> = -12A	-	10.8	-	ns
Rise Time	<b>t<sub>r</sub></b>		-	13.2	-	
Turn-Off Delay Time	<b>t<sub>d(off)</sub></b>		-	73	-	
Fall Time	<b>t<sub>f</sub></b>		-	35	-	
Reverse Recovery Time	<b>t<sub>rr</sub></b>	I <sub>F</sub> = -12A, dI <sub>F</sub> /dt = 100A/μs	-	25	-	ns
Reverse Recovery Charge	<b>Q<sub>rr</sub></b>		-	10	-	nC
<b>Drain-source body diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	<b>V<sub>SD</sub></b>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0V	-	-	-1.2	V
Continuous Source Current	T <sub>A</sub> =25°C	<b>I<sub>S</sub></b>	-	-	-20	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C.
2. The EAS data shows Max. rating . The test condition is V<sub>DD</sub>= -25V, V<sub>GS</sub>= -10V, L=0.1mH, I<sub>AS</sub>= -40A.
3. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.



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Typical Characteristics

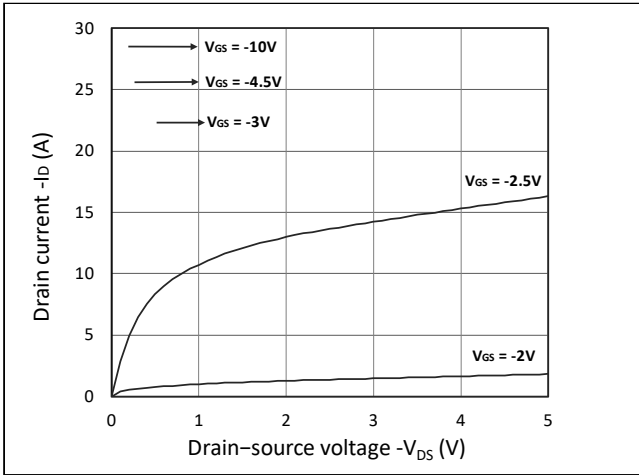


Figure 1. Output Characteristics

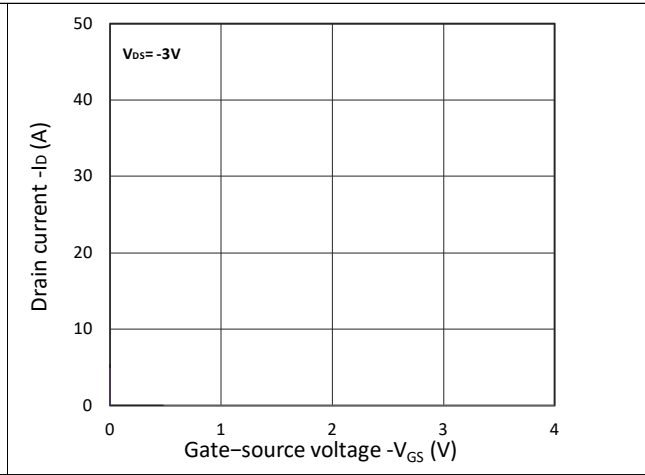


Figure 2. Transfer Characteristics

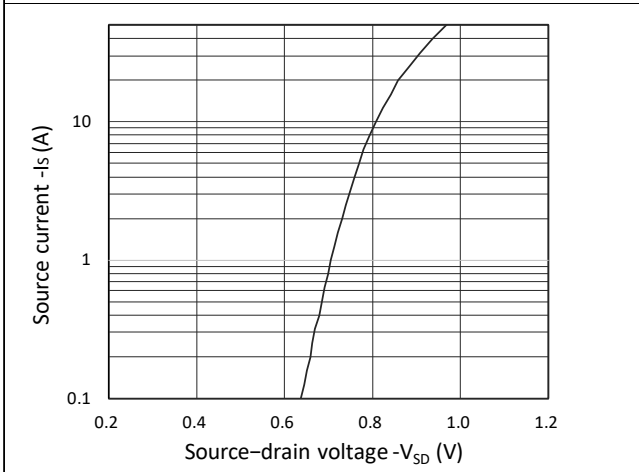


Figure 3. Forward Characteristics of Reverse

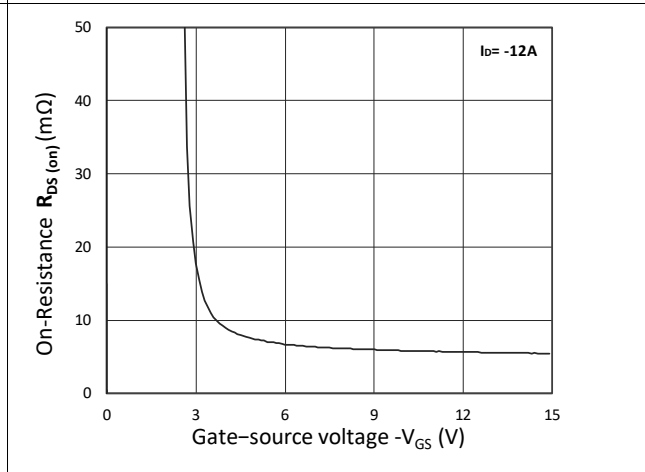


Figure 4.  $R_{DS(on)}$  vs.  $V_{GS}$

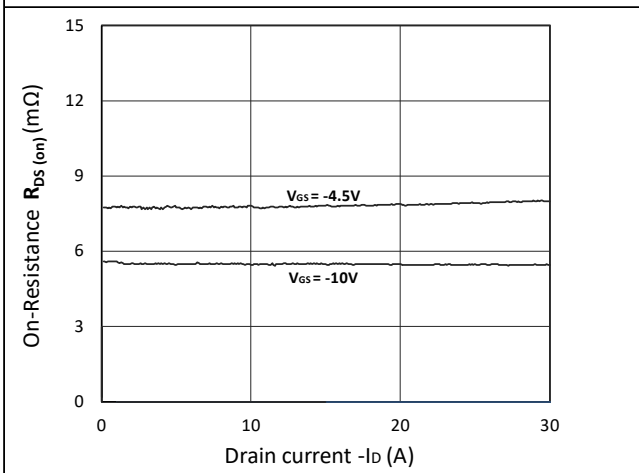


Figure 5.  $R_{DS(on)}$  vs.  $I_D$

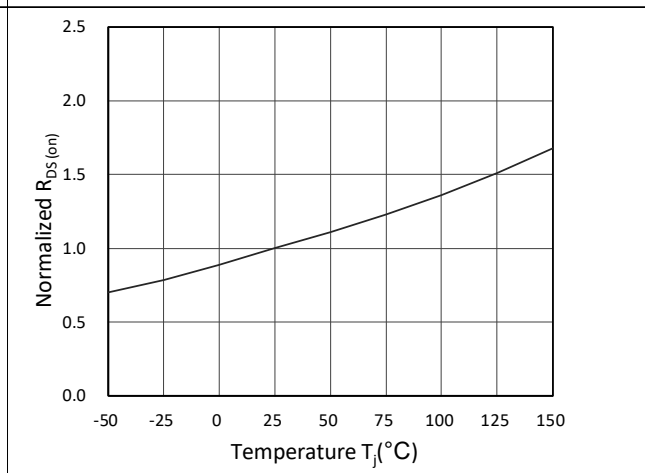


Figure 6. Normalized  $R_{DS(on)}$  vs. Temperature



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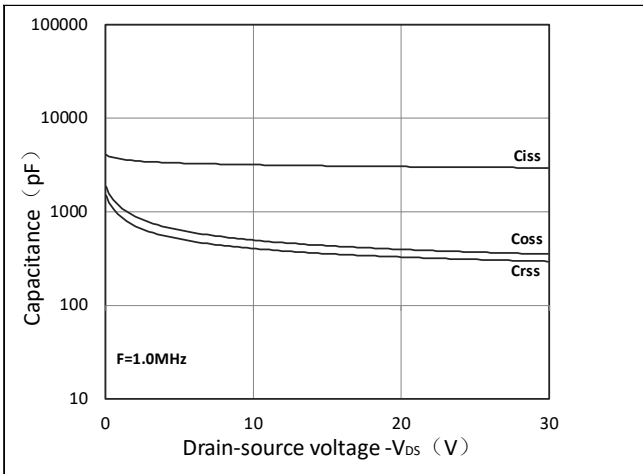


Figure 7. Capacitance Characteristics

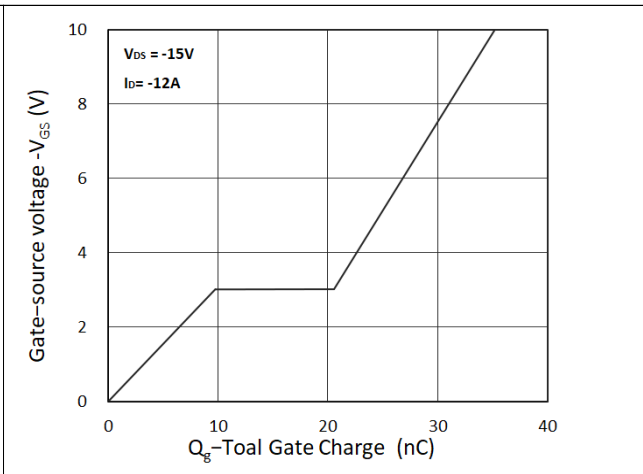


Figure 8. Gate Charge Characteristics

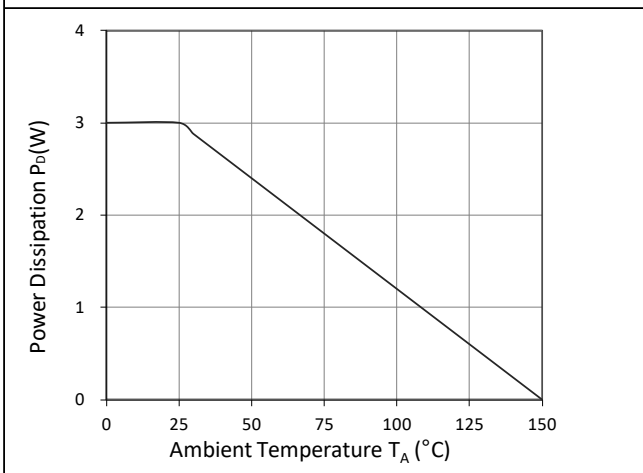


Figure 9. Power Dissipation

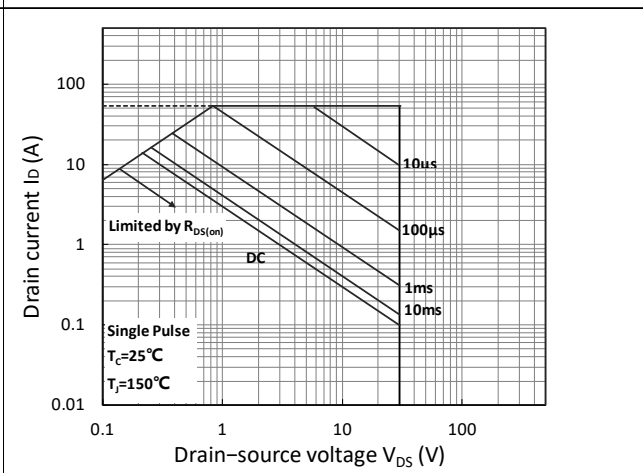


Figure 10. Safe Operating Area

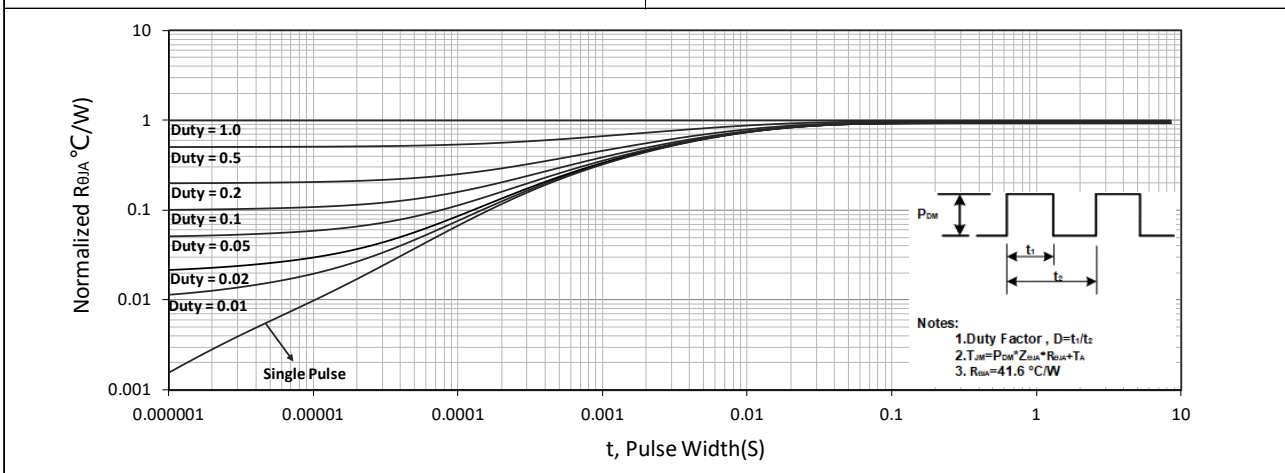


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

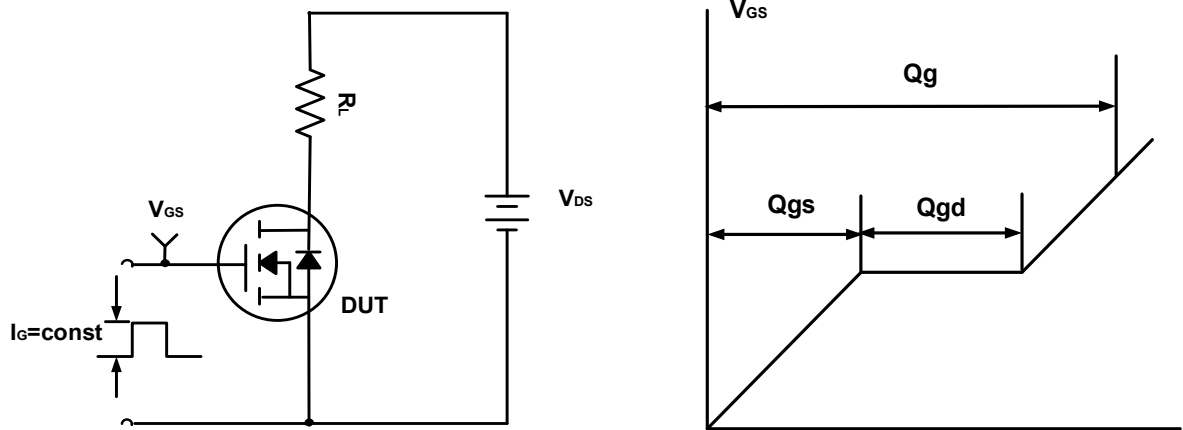


Figure A. Gate Charge Test Circuit & Waveforms

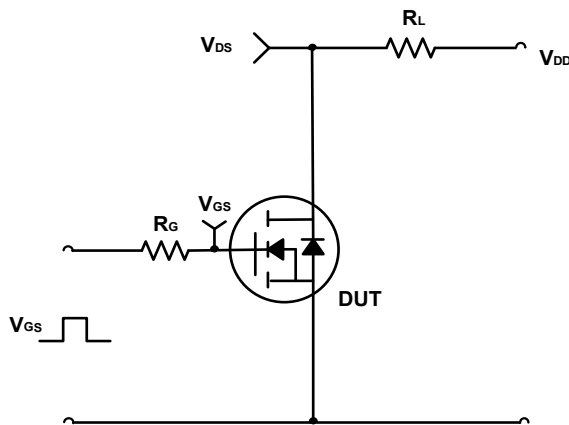


Figure B. Switching Test Circuit & Waveforms

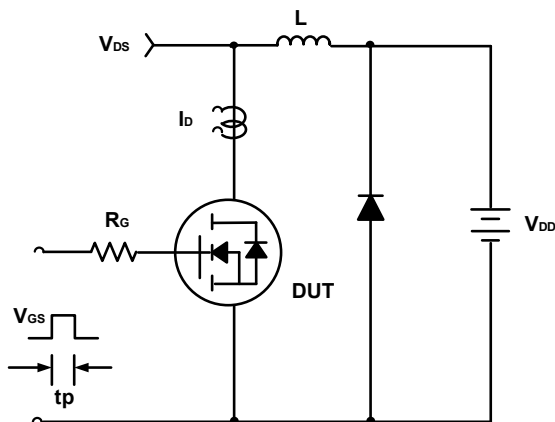
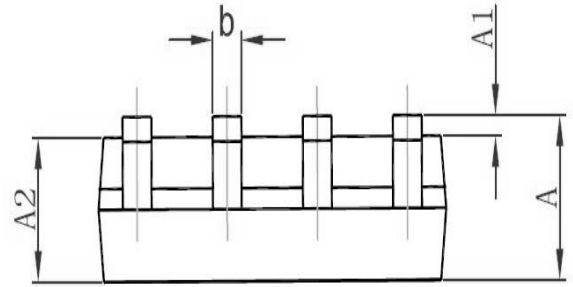
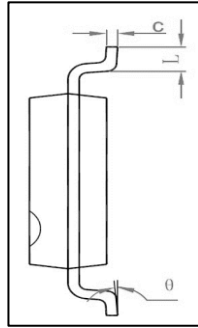
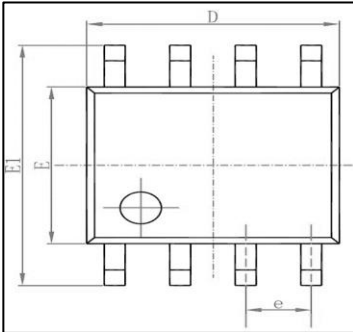
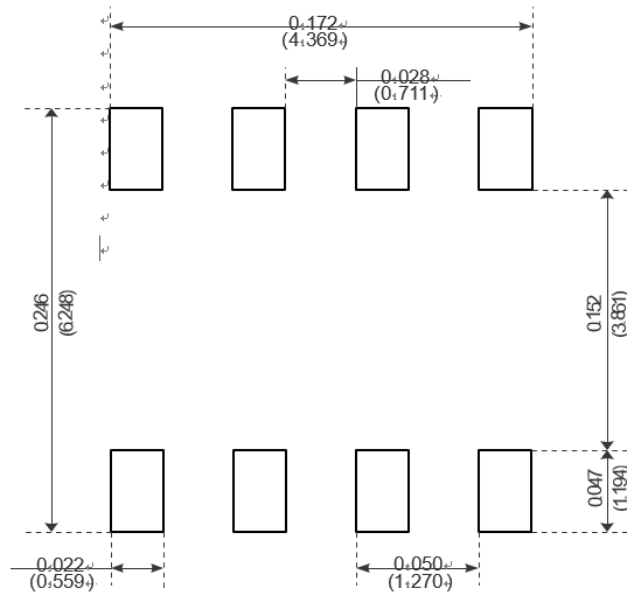


Figure C. Unclamped Inductive Switching Circuit & Waveforms

# Package Mechanical Data:SOP-8L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads